TOSHIBA TC7SZ02AFE

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7SZ02AFE

2 INPUT NOR GATE

FEATURES

 High Output Drive : ±24 mA (Typ.)

 $@V_{CC} = 3 V$

Super High Speed Operation : tpD 2.4 ns (Typ.)

 $@V_{CC} = 5 \text{ V}, 50 \text{ pF}$

Operation Voltage Range : $V_{CC(opr)} = 1.8 \sim 5.5 \text{ V}$

Supply Voltage Data Retention : $V_{CC} = 1.5 \sim 5.5 \text{ V}$

Latch-up Performance : ±500 mA

ESD Performance : Human Body Model > ±2000 V

Machine Model > ±200 V

Power Down Protection is provided on all inputs.

Matches the Performance of TC74LCX Series when

Operated at 3.3 V VCC

Input Rise and Fall Time (tr, tf) (Recommended Operation Condition)

 $@V_{CC} = 1.8 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V} : 0 \sim 20 \text{ ns/V}$ $@V_{CC} = 3.3 V \pm 0.3 V$: 0~10 ns/V $@V_{CC} = 5.5 V \pm 0.5 V$: 0~5 ns/V

MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~6	V
DC Input Voltage	VIN	-0.5~6	V
DC Output Voltage	Vout	-0.5~V _{CC} + 0.5	V
Input Diode Current	Ικ	± 20	mA
Output Diode Current	loк	± 20	mA
DC Output Current	IOUT	± 50	mA
DC V _{CC} /Ground Current	lcc	± 50	mA
Power Dissipation	PD	150	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10 s)	TL	260	°C

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Weight: 0.003 g (Typ.)

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC SYMBOL		TEST CONDITION			Ta = 25°C			$Ta = -40 \sim 85^{\circ}C$		UNIT
				Vсс (V)	MIN.	TYP.	MAX.	MIN.	MAX.	ONIT
High-Level Input Voltage				1.8	0.75 × V _C C		_	0.75 × V _C C	_	V
				2.3 – 5.5	0.7 ×		_	0.7 ×	-	
					V _{CC}		0.25	V _{CC}	0.25	
Low-Level Input Voltage	.,			1.8	-	_	× V _C C	l .	× V _{CC}	.,
	VIL			2.3 – 5.5	_	1	0.3 × V _{CC}		0.3 × VCC	V
				1.8	1.7	1.8	_	1.7	_	
				2.3	2.2	2.3	_	2.2	_	
			$I_{OH} = -100 \mu A$	3.0	2.9	3.0	_	2.9	_	v
High-Level	.,	V _{IN} = V _{IL}		4.5	4.4	4.5	_	4.4	_	
Output Voltage	Vон		$I_{OH} = -8 \text{mA}$	2.3	1.9	2.15		1.9		
			$I_{OH} = -16 \text{mA}$	3.0	2.4	2.8		2.4	_	
			$I_{OH} = -24 \text{mA}$	3.0	2.3	2.68		2.3		
			$I_{OH} = -32 \text{mA}$	4.5	3.8	4.2		3.8		
			V_{IL} $I_{OL} = 8 \text{ mA}$ $I_{OL} = 16 \text{ mA}$	1.8	_	0	0.1	_	0.1	V
				2.3	_	0	0.1	_	0.1	
				3.0	_	0	0.1	_	0.1	
Low-Level Output Voltage	Voi	$V_{IN} = V_{IH}$		4.5	_	0	0.1	_	0.1	
	101	or V _{IL}		2.3	_	0.1	0.3	_	0.3	
				3.0	_	0.15	0.4	_	0.4	
			I _{OL} = 24 mA	3.0	_	0.22	0.55	_	0.55	
			I _{OL} = 32 mA	4.5	_	0.22	0.55	_	0.55	
Input Leakage Current	liN	$V_{IN} = 5.5 V$ or GND		0 – 5.5	_	_	± 1	_	± 10	μΑ
Quiescent Supply Current	lcc	V _{IN} = V _{CC} or GND		5.5	_	_	2	_	20	μΑ

AC ELECTRICAL CHARACTERISTICS (I	Input $t_r = \frac{1}{2}$	$t_f = 3 \text{ ns}$
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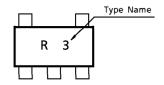
CHARACTERISTIC	SYMBOL	SYMBOL TEST CONDITION		Ta = 25°C		Ta = -4	UNIT		
CHARACTERISTIC	3 TIVIBOL	TEST CONDITION	V _C C (V)	MIN.	TYP.	MAX.	MIN.	MAX.	ONIT
			1.8	2.0	4.4	9.5	2.0	10.0	
		$C_L = 15 pF$,	2.5 ± 0.2	0.8	2.9	6.5	0.8	7.0	
Propagation	t _{PLH}	$R_L = 1 M\Omega$	3.3 ± 0.3	0.5	2.3	4.5	0.5	4.7]
Delay Time t _{PHL}		5.0 ± 0.5	0.5	1.9	3.9	0.5	4.1	ns	
		$C_L = 50 pF$,	3.3 ± 0.3	1.5	2.9	5.0	1.5	5.2	
		$R_L = 500 \Omega$	5.0 ± 0.5	0.8	2.4	4.3	0.8	4.5	
Input Capacitance	C _{IN}		0 - 5.5	_	4	_	_	_	pF
Power Dissipation	C _{PD}	(Note 1)	3.3	_	19	_	_	_	, E
Capacitance		(Note 1)	5.5	_	27	_	_	_	pF

(Note 1): CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

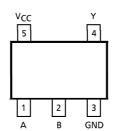
Average operating current can be obtained by the equation.

$$ICC(opr) = CPD \cdot VCC \cdot fIN + ICC$$

MARKING



PIN ASSIGNMENT (TOP VIEW)



TRUTH TABLE

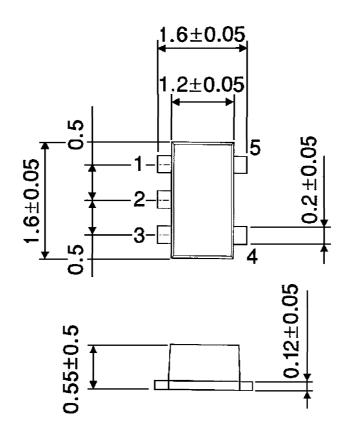
Α	В	Y					
L	L	Н					
L	Н	L					
Н	L	L					
Н	Н	L					

LOGIC DIAGRAM



PACKAGE DIMENSIONS SON5-P-0.50

Unit : mm



Weight: 0.003 g (Typ.)